

Express Mail No. EV670647800US

Docket No.: 384848011US  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re Patent Application of:  
Peng et al.

Application No.: 10/765,802

Allowed: March 8, 2005

Filed: January 26, 2004

Art Unit: 2818

For: HIGH DENSITY SEMICONDUCTOR  
MEMORY CELL AND MEMORY ARRAY  
USING A SINGLE TRANSISTOR AND  
HAVING VARIABLE GATE OXIDE  
BREAKDOWN

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Examiner: G. N. Auduong

**SUBMISSION OF DRAWINGS**

MS Issue Fee  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Submitted herewith is one set (twenty-one sheets, twenty-seven figures) of drawings for filing in the above-identified patent application. Kindly substitute the enclosed drawings for the drawings submitted with the originally filed application.

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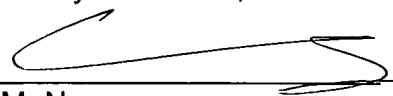
Applicant believes no fee is due with this response. However, if a fee is due, please charge our Deposit Account No. 50-0665, under Order No. 384848011US from which the undersigned is authorized to draw.

Dated:

3/21/05

Respectfully submitted,

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